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Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	81
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	132-WFQFN
Supplier Device Package	132-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl030v5-qng132i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature¹

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T _{STG} (°C) ²	Maximum Operating Junction Temperature T _J (°C) ²
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

- 1. This is a stress rating only; functional operation at any condition other than those indicated is not implied.
- These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 on page 2-2 for device operating conditions and absolute limits.

Table 2-4 • Overshoot and Undershoot Limits 1

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/ Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

- 1. Based on reliability requirements at junction temperature at 85°C.
- 2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
- 3. This table does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every IGLOO device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

IGLOO I/Os are activated only if ALL of the following three conditions are met:

- 1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5).
- 2. VCCI > VCC 0.75 V (typical)
- 3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up (V5 devices): 0.6 V < trip_point_up < 1.2 V Ramping down (V5 Devices): 0.5 V < trip_point_down < 1.1 V Ramping up (V2 devices): 0.75 V < trip_point_up < 1.05 V Ramping down (V2 devices): 0.65 V < trip_point_down < 0.95 V

VCC Trip Point:

Ramping up (V5 devices): 0.6 V < trip_point_up < 1.1 V Ramping down (V5 devices): 0.5 V < trip_point_down < 1.0 V

Ramping up (V2 devices): $0.65 \text{ V} < \text{trip_point_up} < 1.05 \text{ V}$ Ramping down (V2 devices): $0.55 \text{ V} < \text{trip_point_down} < 0.95 \text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V \pm 0.25 V for V5 devices, and 0.75 V \pm 0.2 V for V2 devices), the PLL output lock signal goes low and/or the output clock is lost. Refer to the Brownout Voltage section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC®* and *ProASIC3E* FPGA fabric user guides for information on clock and lock recovery.

Internal Power-Up Activation Sequence

- 1. Core
- 2. Input buffers
- 3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

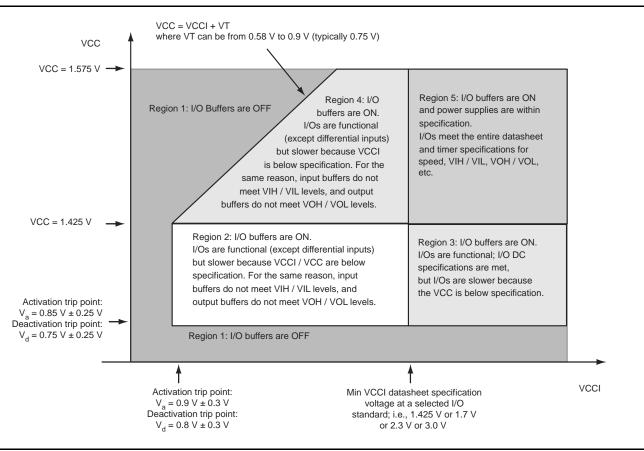


Figure 2-1 • V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels

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Temperature and Voltage Derating Factors

Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.425 V) For IGLOO V2 or V5 devices, 1.5 V DC Core Supply Voltage

Array Voltage VCC		Junction Temperature (°C)											
(V)	-40°C	0°C	25°C	70°C	85°C	100°C							
1.425	0.934	0.953	0.971	1.000	1.007	1.013							
1.500	0.855	0.874	0.891	0.917	0.924	0.929							
1.575	0.799	0.816	0.832	0.857	0.864	0.868							

Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.14 V) For IGLOO V2, 1.2 V DC Core Supply Voltage

Array Voltage VCC		Junction Temperature (°C)											
(V)	−40°C	0°C	25°C	70°C	85°C	100°C							
1.14	0.967	0.978	0.991	1.000	1.006	1.010							
1.20	0.864	0.874	0.885	0.894	0.899	0.902							
1.26	0.794	0.803	0.814	0.821	0.827	0.830							

Calculating Power Dissipation

Quiescent Supply Current

Quiescent supply current (IDD) calculation depends on multiple factors, including operating voltages (VCC, VCCI, and VJTAG), operating temperature, system clock frequency, and power modes usage. Microsemi recommends using the PowerCalculator and SmartPower software estimation tools to evaluate the projected static and active power based on the user design, power mode usage, operating voltage, and temperature.

Table 2-8 • Power Supply State per Mode

		Pov	ver Supply Config	urations	
Modes/power supplies	vcc	VCCPLL	VCCI	VJTAG	VPUMP
Flash*Freeze	On	On	On	On	On/off/floating
Sleep	Off	Off	On	Off	Off
Shutdown	Off	Off	Off	Off	Off
No Flash*Freeze	On	On	On	On	On/off/floating

Note: Off: Power supply level = 0 V

Table 2-9 • Quiescent Supply Current (IDD) Characteristics, IGLOO Flash*Freeze Mode*

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
Typical	1.2 V	4	4	8	13	20	27	30	44	μΑ
(25°C)	1.5 V	6	6	10	18	34	51	72	127	μΑ

Note: *IDD includes VCC, VPUMP, VCCI, VCCPLL, and VMV currents. Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

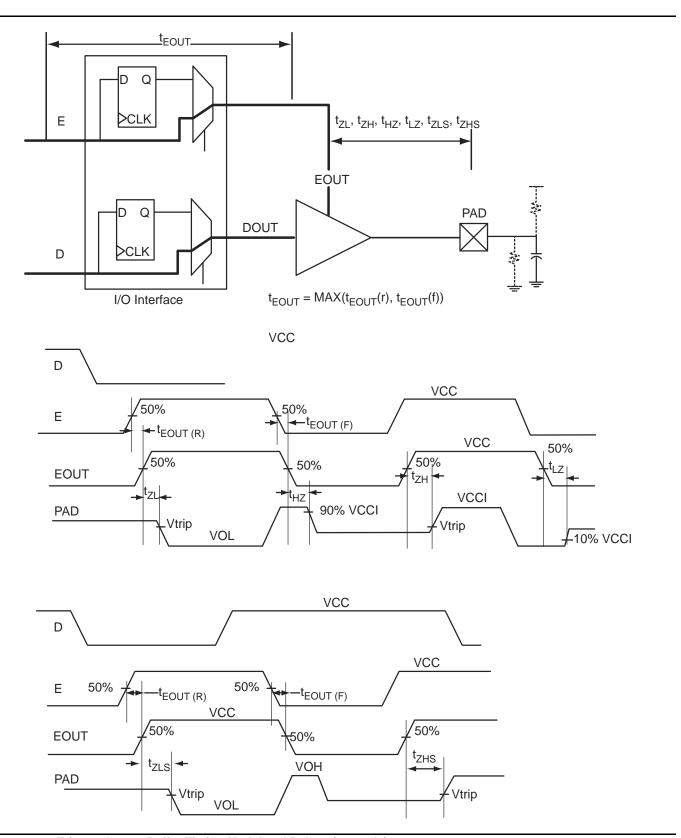


Figure 2-6 • Tristate Output Buffer Timing Model and Delays (example)

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Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-25 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings
Applicable to Advanced I/O Banks

		Equivalent			VIL	VIH		VOL	VOH	IOL ¹	IOH ¹
I/O Standard	Drive Strength	Software Default Drive Strength Option ²	Slew Rate	Min.V	Max. V	Min. V	Max.V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	-0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range ³	100 μΑ	12 mA	High	-0.3	0.8	2	3.6	0.2	VCCI - 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	-0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI - 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	-0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12
1.2 V LVCMOS ⁴	2 mA	2 mA	High	-0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range ^{4,5}	100 μΑ	2 mA	High	-0.3	0.3 * VCCI	0.7 * VCCI	1.575	0.1	VCCI - 0.1	0.1	0.1
3.3 V PCI					Per P	CI specificatio	ns				
3.3 V PCI-X	Per PCI-X specifications										

Notes:

- 1. Currents are measured at 85°C junction temperature.
- 2. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
- 3. All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
- 4. Applicable to V2 Devices operating at VCCI ≥ VCC.
- 5. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.

Table 2-49 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		V _{OL}	VOH	VOH IOL		IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μ Α ⁴	μA ⁴
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10

Notes:

- 1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.
- 2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges
- 3. Currents are measured at 100°C junction temperature and maximum voltage.
- 4. Currents are measured at 85°C junction temperature.
- 5. Software default selection highlighted in gray.

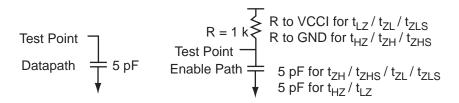


Figure 2-7 • AC Loading

Table 2-50 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	3.3	1.4	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-67 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
100 μΑ	2 mA	Std.	0.97	6.61	0.18	1.19	0.66	6.63	5.63	3.15	2.98	10.22	9.23	ns
100 μΑ	4 mA	Std.	0.97	6.61	0.18	1.19	0.66	6.63	5.63	3.15	2.98	10.22	9.23	ns
100 μΑ	6 mA	Std.	0.97	5.49	0.18	1.19	0.66	5.51	4.84	3.54	3.66	9.10	8.44	ns
100 μΑ	8 mA	Std.	0.97	5.49	0.18	1.19	0.66	5.51	4.84	3.54	3.66	9.10	8.44	ns
100 μΑ	12 mA	Std.	0.97	4.69	0.18	1.19	0.66	4.71	4.25	3.80	4.10	8.31	7.85	ns
100 μΑ	16 mA	Std.	0.97	4.46	0.18	1.19	0.66	4.48	4.11	3.86	4.21	8.07	7.71	ns
100 μΑ	24 mA	Std.	0.97	4.34	0.18	1.19	0.66	4.36	4.14	3.93	4.64	7.95	7.74	ns

Notes:

- The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 μA. Drive strengths
 displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
- 2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-68 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
100 μΑ	2 mA	Std.	0.97	3.92	0.18	1.19	0.66	3.94	3.10	3.16	3.17	7.54	6.70	ns
100 μΑ	4 mA	Std.	0.97	3.92	0.18	1.19	0.66	3.94	3.10	3.16	3.17	7.54	6.70	ns
100 μΑ	6 mA	Std.	0.97	3.28	0.18	1.19	0.66	3.30	2.54	3.54	3.86	6.90	6.14	ns
100 μΑ	8 mA	Std.	0.97	3.28	0.18	1.19	0.66	3.30	2.54	3.54	3.86	6.90	6.14	ns
100 μΑ	12 mA	Std.	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
100 μΑ	16 mA	Std.	0.97	2.87	0.18	1.19	0.66	2.89	2.22	3.86	4.41	6.49	5.82	ns
100 μΑ	24 mA	Std.	0.97	2.90	0.18	1.19	0.66	2.92	2.16	3.94	4.86	6.51	5.75	ns

Notes:

- 1. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.
- 2. Software default selection highlighted in gray.
- 3. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is \pm 100 μ A. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

Table 2-75 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7

Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
100 μΑ	2 mA	Std.	1.55	6.69	0.26	1.32	1.10	6.69	5.73	3.41	3.72	12.48	11.52	ns
100 μΑ	4 mA	Std.	1.55	6.69	0.26	1.32	1.10	6.69	5.73	3.41	3.72	12.48	11.52	ns
100 μΑ	6 mA	Std.	1.55	5.58	0.26	1.32	1.10	5.58	5.01	3.77	4.35	11.36	10.79	ns
100 μΑ	8 mA	Std.	1.55	5.58	0.26	1.32	1.10	5.58	5.01	3.77	4.35	11.36	10.79	ns
100 μΑ	12 mA	Std.	1.55	4.82	0.26	1.32	1.10	4.82	4.44	4.02	4.76	10.61	10.23	ns
100 μΑ	16 mA	Std.	1.55	4.82	0.26	1.32	1.10	4.82	4.44	4.02	4.76	10.61	10.23	ns

Notes:

- 1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 μA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
- 2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-76 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
100 µA	2 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.30	3.40	3.92	9.89	9.09	ns
100 µA	4 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.30	3.40	3.92	9.89	9.09	ns
100 µA	6 mA	Std.	1.55	3.51	0.26	1.32	1.10	3.51	2.79	3.76	4.56	9.30	8.57	ns
100 µA	8 mA	Std.	1.55	3.51	0.26	1.32	1.10	3.51	2.79	3.76	4.56	9.30	8.57	ns
100 μΑ	12 mA	Std.	1.55	3.20	0.26	1.32	1.10	3.20	2.52	4.01	4.97	8.99	8.31	ns
100 µA	16 mA	Std.	1.55	3.20	0.26	1.32	1.10	3.20	2.52	4.01	4.97	8.99	8.31	ns

Notes:

- The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 μA. Drive strengths
 displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
- 2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.
- 3. Software default selection highlighted in gray.

Table 2-81 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

2.5 V LVCMOS	v	ΊL	v	IH	VOL	VOH	IOL	ЮН	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μ Α ⁴
2 mA	-0.3	0.7	1.7	3.6	0.7	1.7	2	2	16	18	10	10
4 mA	-0.3	0.7	1.7	3.6	0.7	1.7	4	4	16	18	10	10
6 mA	-0.3	0.7	1.7	3.6	0.7	1.7	6	6	32	37	10	10
8 mA	-0.3	0.7	1.7	3.6	0.7	1.7	8	8	32	37	10	10

Notes:

- 1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.
- 2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges
- 3. Currents are measured at 100°C junction temperature and maximum voltage.
- 4. Currents are measured at 85°C junction temperature.
- 5. Software default selection highlighted in gray.

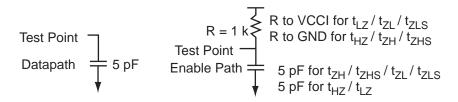


Figure 2-8 • AC Loading

Table 2-82 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	2.5	1.2	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

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Input Register

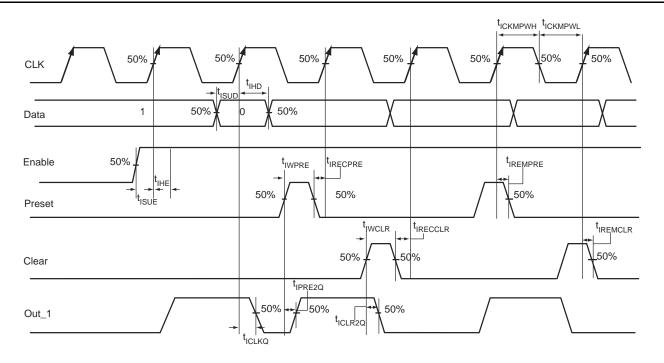


Figure 2-18 • Input Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-157 • Input Data Register Propagation Delays

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t _{ICLKQ}	Clock-to-Q of the Input Data Register	0.42	ns
t _{ISUD}	Data Setup Time for the Input Data Register	0.47	ns
t _{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t _{ISUE}	Enable Setup Time for the Input Data Register	0.67	ns
t _{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t _{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
t _{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
t _{IREMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
t _{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
t _{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
t _{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t _{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t _{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register		ns
t _{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
t _{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

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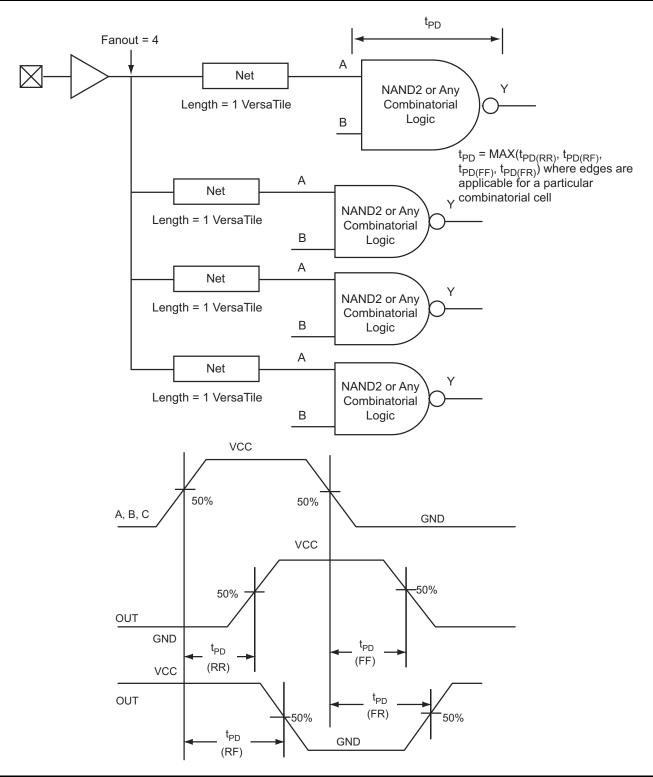


Figure 2-26 • Timing Model and Waveforms

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Table 2-185 • AGL250 Global Resource

Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

		Std.		
Parameter	Description	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	2.11	2.57	ns
t _{RCKH}	Input High Delay for Global Clock	2.19	2.81	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.40		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.65		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

- 1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
- 2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
- 3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-186 • AGL400 Global Resource

Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

		Std.		
Parameter	Description	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	2.18	2.64	ns
t _{RCKH}	Input High Delay for Global Clock	2.27	2.89	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.40		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.65		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

- 1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
- 2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
- 3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

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The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO a devices. The Flash*Freeze pin location is independent of device, allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO FPGA Fabric User Guide* for more information on I/O states during Flash*Freeze mode.

Table 3-1 • Flash*Freeze Pin Location in IGLOO Family Packages (device-independent)

IGLOO Packages	Flash*Freeze Pin
CS81/UC81	H2
CS121	J5
CS196	P3
CS281	W2
QN48	14
QN68	18
QN132	B12
VQ100	27
FG144	L3
FG256	Т3
FG484	W6

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IGLOO Low Power Flash FPGAs

CS196				
Pin Number	AGL125 Function			
H11	GCB0/IO54RSB0			
H12	GCA1/IO55RSB0			
H13	IO49RSB0			
H14	GCA2/IO57RSB0			
J1	GFC2/IO115RSB1			
J2	IO110RSB1			
J3	IO94RSB1			
J4	IO93RSB1			
J5	IO89RSB1			
J6	NC			
J7	VCC			
J8	VCC			
J9	NC			
J10	IO60RSB0			
J11	GCB2/IO58RSB0			
J12	IO50RSB0			
J13	GDC1/IO61RSB0			
J14	GDC0/IO62RSB0			
K1	IO99RSB1			
K2	GND			
K3	IO95RSB1			
K4	VCCIB1			
K5	NC			
K6	IO86RSB1			
K7	IO80RSB1			
K8	IO74RSB1			
K9	IO72RSB1			
K10	NC			
K11	VCCIB0			
K12	GDA1/IO65RSB0			
K13	GND			
K14	GDB1/IO63RSB0			
L1	GEB1/IO107RSB1			
L2	GEC1/IO109RSB1			
L3	GEC0/IO108RSB1			

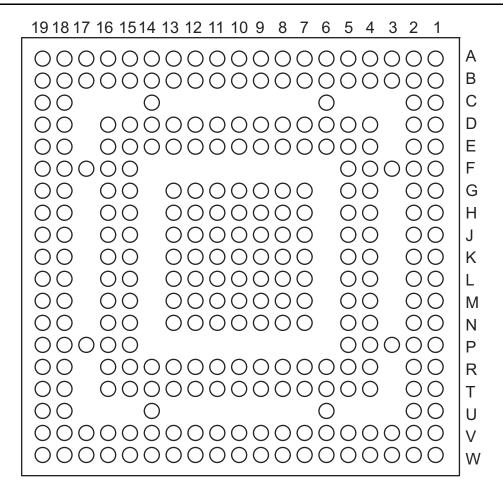
	CS196
Pin Number	AGL125 Function
L5	IO91RSB1
L6	IO90RSB1
L7	IO83RSB1
L8	IO81RSB1
L9	IO71RSB1
L10	IO70RSB1
L11	VPUMP
L12	VJTAG
L13	GDA0/IO66RSB0
L14	GDB0/IO64RSB0
M1	GEB0/IO106RSB1
M2	GEA1/IO105RSB1
M3	GNDQ
M4	VCCIB1
M5	IO92RSB1
M6	IO88RSB1
M7	NC
M8	VCCIB1
M9	IO76RSB1
M10	GDB2/IO68RSB1
M11	VCCIB1
M12	VMV1
M13	TRST
M14	VCCIB0
N1	GEA0/IO104RSB1
N2	VMV1
N3	GEC2/IO101RSB1
N4	IO100RSB1
N5	GND
N6	IO87RSB1
N7	IO82RSB1
N8	IO78RSB1
N9	IO73RSB1
N10	GND
N11	TCK
N12	TDI
'1'2	15.

	CS196
Pin Number	AGL125 Function
N13	GNDQ
N14	TDO
P1	GND
P2	GEA2/IO103RSB1
P3	FF/GEB2/IO102RSB1
P4	IO98RSB1
P5	IO97RSB1
P6	IO85RSB1
P7	IO84RSB1
P8	IO79RSB1
P9	IO77RSB1
P10	IO75RSB1
P11	GDC2/IO69RSB1
P12	GDA2/IO67RSB1
P13	TMS
P14	GND



Package Pin Assignments

CS281



Note: This is the bottom view of the package.

Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.

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IGLOO Low Power Flash FPGAs

VQ100				
Pin Number	AGL060 Function			
1	GND			
2	GAA2/IO51RSB1			
3	IO52RSB1			
4	GAB2/IO53RSB1			
5	IO95RSB1			
6	GAC2/IO94RSB1			
7	IO93RSB1			
8	IO92RSB1			
9	GND			
10	GFB1/IO87RSB1			
11	GFB0/IO86RSB1			
12	VCOMPLF			
13	GFA0/IO85RSB1			
14	VCCPLF			
15	GFA1/IO84RSB1			
16	GFA2/IO83RSB1			
17	VCC			
18	VCCIB1			
19	GEC1/IO77RSB1			
20	GEB1/IO75RSB1			
21	GEB0/IO74RSB1			
22	GEA1/IO73RSB1			
23	GEA0/IO72RSB1			
24	VMV1			
25	GNDQ			
26	GEA2/IO71RSB1			
27	FF/GEB2/IO70RSB1			
28	GEC2/IO69RSB1			
29	IO68RSB1			
30	IO67RSB1			
31	IO66RSB1			
32	IO65RSB1			
33	IO64RSB1			
34	IO63RSB1			
35	IO62RSB1			
36	IO61RSB1			

VQ100		
Pin Number AGL060 Function		
37	VCC	
38	GND	
39	VCCIB1	
40	IO60RSB1	
41	IO59RSB1	
42	IO58RSB1	
43	IO57RSB1	
44	GDC2/IO56RSB1	
45	GDB2/IO55RSB1	
46	GDA2/IO54RSB1	
47	TCK	
48	TDI	
49	TMS	
50	VMV1	
51	GND	
52	VPUMP	
53	NC	
54	TDO	
55	TRST	
56	VJTAG	
57	GDA1/IO49RSB0	
58	GDC0/IO46RSB0	
59	GDC1/IO45RSB0	
60	GCC2/IO43RSB0	
61	GCB2/IO42RSB0	
62	GCA0/IO40RSB0	
63	GCA1/IO39RSB0	
64	GCC0/IO36RSB0	
65	GCC1/IO35RSB0	
66	VCCIB0	
67	GND	
68	VCC	
69	IO31RSB0	
70	GBC2/IO29RSB0	
71	GBB2/IO27RSB0	
72	IO26RSB0	

VQ100		
Pin Number	AGL060 Function	
73	GBA2/IO25RSB0	
74	VMV0	
75	GNDQ	
76	GBA1/IO24RSB0	
77	GBA0/IO23RSB0	
78	GBB1/IO22RSB0	
79	GBB0/IO21RSB0	
80	GBC1/IO20RSB0	
81	GBC0/IO19RSB0	
82	IO18RSB0	
83	IO17RSB0	
84	IO15RSB0	
85	IO13RSB0	
86	IO11RSB0	
87	VCCIB0	
88	GND	
89	VCC	
90	IO10RSB0	
91	IO09RSB0	
92	IO08RSB0	
93	GAC1/IO07RSB0	
94	GAC0/IO06RSB0	
95	GAB1/IO05RSB0	
96	GAB0/IO04RSB0	
97	GAA1/IO03RSB0	
98	GAA0/IO02RSB0	
99	IO01RSB0	
100	IO00RSB0	



Package Pin Assignments

VQ100		
Pin Number	AGL125 Function	
1	GND	
2	GAA2/IO67RSB1	
3	IO68RSB1	
4	GAB2/IO69RSB1	
5	IO132RSB1	
6	GAC2/IO131RSB1	
7	IO130RSB1	
8	IO129RSB1	
9	GND	
10	GFB1/IO124RSB1	
11	GFB0/IO123RSB1	
12	VCOMPLF	
13	GFA0/IO122RSB1	
14	VCCPLF	
15	GFA1/IO121RSB1	
16	GFA2/IO120RSB1	
17	VCC	
18	VCCIB1	
19	GEC0/IO111RSB1	
20	GEB1/IO110RSB1	
21	GEB0/IO109RSB1	
22	GEA1/IO108RSB1	
23	GEA0/IO107RSB1	
24	VMV1	
25	GNDQ	
26	GEA2/IO106RSB1	
27	FF/GEB2/IO105RSB 1	
28	GEC2/IO104RSB1	
29	IO102RSB1	
30	IO100RSB1	
31	IO99RSB1	
32	IO97RSB1	
33	IO96RSB1	
34	IO95RSB1	
35	IO94RSB1	

VQ100		
Pin Number AGL125 Function		
36	IO93RSB1	
37	VCC	
38	GND	
39	VCCIB1	
40	IO87RSB1	
41	IO84RSB1	
42	IO81RSB1	
43	IO75RSB1	
44	GDC2/IO72RSB1	
45	GDB2/IO71RSB1	
46	GDA2/IO70RSB1	
47	TCK	
48	TDI	
49	TMS	
50	VMV1	
51	GND	
52	VPUMP	
53	NC	
54	TDO	
55	TRST	
56	VJTAG	
57	GDA1/IO65RSB0	
58	GDC0/IO62RSB0	
59	GDC1/IO61RSB0	
60	GCC2/IO59RSB0	
61	GCB2/IO58RSB0	
62	GCA0/IO56RSB0	
63	GCA1/IO55RSB0	
64	GCC0/IO52RSB0	
65	GCC1/IO51RSB0	
66	VCCIB0	
67	GND	
68	VCC	
69	IO47RSB0	
70	GBC2/IO45RSB0	
71	GBB2/IO43RSB0	

VQ100		
Pin Number	AGL125 Function	
72	IO42RSB0	
73	GBA2/IO41RSB0	
74	VMV0	
75	GNDQ	
76	GBA1/IO40RSB0	
77	GBA0/IO39RSB0	
78	GBB1/IO38RSB0	
79	GBB0/IO37RSB0	
80	GBC1/IO36RSB0	
81	GBC0/IO35RSB0	
82	IO32RSB0	
83	IO28RSB0	
84	IO25RSB0	
85	IO22RSB0	
86	IO19RSB0	
87	VCCIB0	
88	GND	
89	VCC	
90	IO15RSB0	
91	IO13RSB0	
92	IO11RSB0	
93	IO09RSB0	
94	IO07RSB0	
95	GAC1/IO05RSB0	
96	GAC0/IO04RSB0	
97	GAB1/IO03RSB0	
98	GAB0/IO02RSB0	
99	GAA1/IO01RSB0	
100	GAA0/IO00RSB0	

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IGLOO Low Power Flash FPGAs

FG144			FG144		FG144	
Pin Number	AGL400 Function	Pin Number	AGL400 Function	Pin Number	AGL400 Function	
A1	GNDQ	D1	IO149NDB3	G1	GFA1/IO145PPB3	
A2	VMV0	D2	IO149PDB3	G2	GND	
A3	GAB0/IO02RSB0	D3	IO153VDB3	G3	VCCPLF	
A4	GAB1/IO03RSB0	D4	GAA2/IO155UPB3	G4	GFA0/IO145NPB3	
A5	IO16RSB0	D5	GAC0/IO04RSB0	G5	GND	
A6	GND	D6	GAC1/IO05RSB0	G6	GND	
A7	IO30RSB0	D7	GBC0/IO54RSB0	G7	GND	
A8	VCC	D8	GBC1/IO55RSB0	G8	GDC1/IO77UPB1	
A9	IO34RSB0	D9	GBB2/IO61PDB1	G9	IO72NDB1	
A10	GBA0/IO58RSB0	D10	IO61NDB1	G10	GCC2/IO72PDB1	
A11	GBA1/IO59RSB0	D11	IO62NPB1	G11	IO71NDB1	
A12	GNDQ	D12	GCB1/IO68PPB1	G12	GCB2/IO71PDB1	
B1	GAB2/IO154UDB3	E1	VCC	H1	VCC	
B2	GND	E2	GFC0/IO147NDB3	H2	GFB2/IO143PDB3	
В3	GAA0/IO00RSB0	E3	GFC1/IO147PDB3	H3	GFC2/IO142PSB3	
B4	GAA1/IO01RSB0	E4	VCCIB3	H4	GEC1/IO137PDB3	
B5	IO14RSB0	E5	IO155VPB3	H5	VCC	
B6	IO19RSB0	E6	VCCIB0	H6	IO75PDB1	
B7	IO23RSB0	E7	VCCIB0	H7	IO75NDB1	
B8	IO31RSB0	E8	GCC1/IO67PDB1	H8	GDB2/IO81RSB2	
В9	GBB0/IO56RSB0	E9	VCCIB1	H9	GDC0/IO77VPB1	
B10	GBB1/IO57RSB0	E10	VCC	H10	VCCIB1	
B11	GND	E11	GCA0/IO69NDB1	H11	IO73PSB1	
B12	VMV1	E12	IO70NDB1	H12	VCC	
C1	IO154VDB3	F1	GFB0/IO146NPB3	J1	GEB1/IO136PDB3	
C2	GFA2/IO144PPB3	F2	VCOMPLF	J2	IO143NDB3	
C3	GAC2/IO153UDB3	F3	GFB1/IO146PPB3	J3	VCCIB3	
C4	VCC	F4	IO144NPB3	J4	GEC0/IO137NDB3	
C5	IO12RSB0	F5	GND	J5	IO125RSB2	
C6	IO17RSB0	F6	GND	J6	IO116RSB2	
C7	IO25RSB0	F7	GND	J7	VCC	
C8	IO32RSB0	F8	GCC0/IO67NDB1	J8	TCK	
C9	IO53RSB0	F9	GCB0/IO68NPB1	J9	GDA2/IO80RSB2	
C10	GBA2/IO60PDB1	F10	GND	J10	TDO	
C11	IO60NDB1	F11	GCA1/IO69PDB1	J11	GDA1/IO79UDB1	
C12	GBC2/IO62PPB1	F12	GCA2/IO70PDB1	J12	GDB1/IO78UDB1	



Package Pin Assignments

FG256		
Pin Number	AGL400 Function	
R5	IO123RSB2	
R6	IO118RSB2	
R7	IO112RSB2	
R8	IO106RSB2	
R9	IO100RSB2	
R10	IO96RSB2	
R11	IO89RSB2	
R12	IO85RSB2	
R13	GDB2/IO81RSB2	
R14	TDI	
R15	NC	
R16	TDO	
T1	GND	
T2	IO126RSB2	
T3	FF/GEB2/IO133RSB2	
T4	IO124RSB2	
T5	IO116RSB2	
T6	IO113RSB2	
T7	IO107RSB2	
T8	IO105RSB2	
Т9	IO102RSB2	
T10	IO97RSB2	
T11	IO92RSB2	
T12	GDC2/IO82RSB2	
T13	IO86RSB2	
T14	GDA2/IO80RSB2	
T15	TMS	
T16	GND	

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